

Notice of References Cited	Application/Control No. 10/042,924	Applicant(s)/Patent Under Reexamination FORBES, LEONARD	
	Examiner William C. Vesperman	Art Unit 2813	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,245,613	06-2001	Hsu et al.	438/259
*	B	US-6,515,328	02-2003	Yang et al.	257/315
*	C	US-6,383,939	05-2002	Yang et al.	438/706
*	D	US-2003/0001197	01-2003	Chang et al.	257/315
*	E	US-5,869,370	02-1999	Chuang et al.	438/264
*	F	US-6,246,089	06-2001	Lin et al.	257/315
*	G	US-6,316,316	11-2001	Wu, Shye-Lin	438/260
*	H	US-2003/0201491	10-2003	Chung, Byung-Hong	257/324
*	I	US-5,408,115	04-1995	Chang, Kuo-Tung	257/324
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Tunneling Leakage Current in Ultrathin Nitride/Oxide Stack Dielectrics, by Ying Shi, Xiewen Wang and T. P. Ma , Published IEEE, 1998, Pages 388-390 (IDS)
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.